

2N5550  
2N5551

SILICON  
NPN TRANSISTORS



TO-92 CASE



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N5550 and 2N5551 are silicon NPN transistors designed for high voltage amplifier applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

	SYMBOL	2N5550	2N5551	UNITS
Collector-Base Voltage	$V_{CB0}$	160	180	V
Collector-Emitter Voltage	$V_{CEO}$	140	160	V
Emitter-Base Voltage	$V_{EBO}$		6.0	V
Continuous Collector Current	$I_C$		600	mA
Power Dissipation	$P_D$		625	mW
Power Dissipation ( $T_C=25^{\circ}\text{C}$ )	$P_D$		1.0	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$		-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\theta_{JA}$		200	$^{\circ}\text{C}/\text{W}$
Thermal Resistance	$\theta_{JC}$		125	$^{\circ}\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5550		2N5551		UNITS
		MIN	MAX	MIN	MAX	
$I_{CBO}$	$V_{CB}=100\text{V}$	-	100	-	-	nA
$I_{CBO}$	$V_{CB}=120\text{V}$	-	-	-	50	nA
$I_{CBO}$	$V_{CB}=100\text{V}, T_A=100^{\circ}\text{C}$	-	100	-	-	$\mu\text{A}$
$I_{CBO}$	$V_{CB}=120\text{V}, T_A=100^{\circ}\text{C}$	-	-	-	50	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=4.0\text{V}$	-	50	-	50	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	160	-	180	-	V
$BV_{CEO}$	$I_C=1.0\text{mA}$	140	-	160	-	V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0	-	6.0	-	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	-	0.15	-	0.15	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	0.25	-	0.20	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	-	1.0	-	1.0	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	1.2	-	1.0	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	60	-	80	-	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	60	250	80	250	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	20	-	30	-	
$h_{fe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	200	50	200	
$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	300	100	300	MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$	-	6.0	-	6.0	pF
$C_{ib}$	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	30	-	20	pF
NF	$V_{CE}=5.0\text{V}, I_C=250\mu\text{A}, R_S=1.0\Omega, f=10\text{Hz to } 15.7\text{kHz}$	-	10	-	8.0	dB

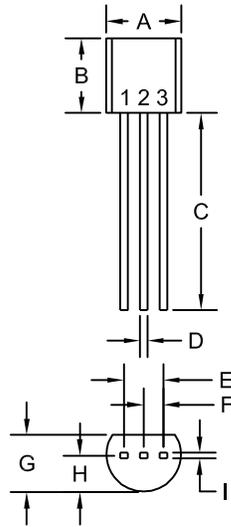
R1 (2-December 2014)

2N5550  
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TO-92 CASE - MECHANICAL OUTLINE



R1

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:  
FULL PART NUMBER

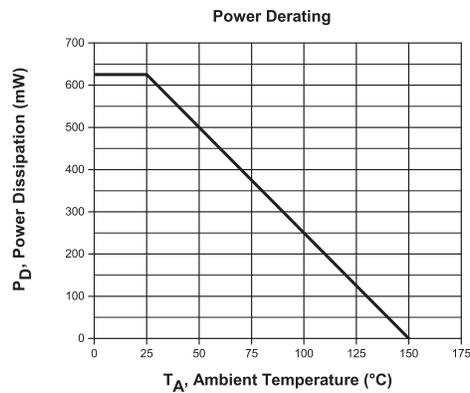
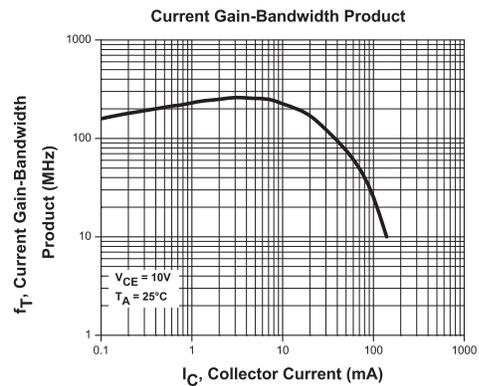
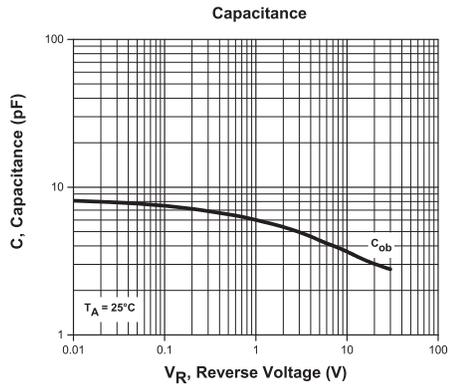
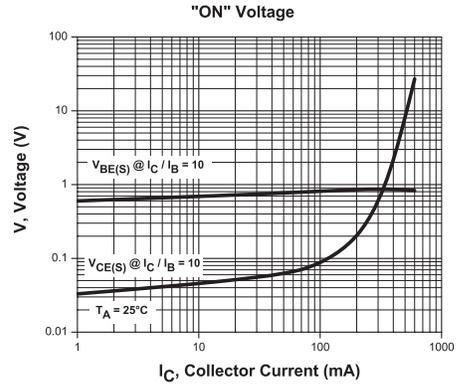
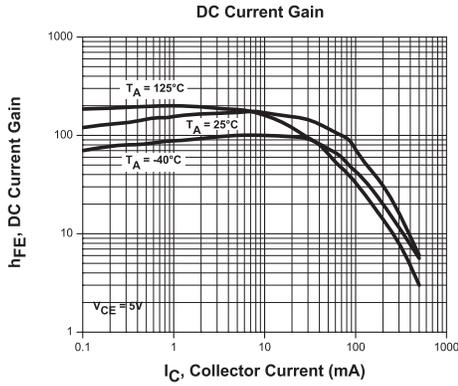
R1 (2-December 2014)

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TYPICAL ELECTRICAL CHARACTERISTICS



R1 (2-December 2014)

## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

#### Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.  
145 Adams Avenue  
Hauppauge, NY 11788 USA  
Main Tel: (631) 435-1110  
Main Fax: (631) 435-1824  
Support Team Fax: (631) 435-3388  
[www.centrasemi.com](http://www.centrasemi.com)

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[www.centrasemi.com/wwreps](http://www.centrasemi.com/wwreps)

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